

C1
Cmt.

characterized in that the fluorine concentration of the SiOF insulating film at a wiring gap portion is set to be higher than the fluorine concentration of the SiOF insulating film on the upper side of the wirings.

C2

3. (Amended) The semiconductor device as claimed in Claim 1, wherein the thickness of the first SiOF film at a center of the wiring gap portion is within the range of 1/3 to 1/1 times of the thickness of the wirings.

C3

5. (Amended) A semiconductor device having a plurality of wiring layers each having a plurality of wirings juxtaposed with one another and a SiOF interlayer insulating film, characterized in that the fluorine concentration of the SiOF interlayer insulating film at a wiring gap portion is set to be higher than the fluorine concentration of the SiOF interlayer insulating film on the upper side of the wirings.

C4

7. (Amended) The semiconductor device as claimed in Claim 5, wherein the thickness of the first SiOF film at a center of the wiring gap portion is within the range of 1/3 to 1/1 times of the thickness of the wirings.

REMARKS

In the Office Action, Claims 1-3 and 5-7 are rejected under 35 U.S.C. §103(a), as allegedly unpatentable over applicants' admitted prior art figures in view of Usami, et al., Japanese Publication No. 10-056009 ("Usami, et al."). The Office Action has also rejected Claims 4 and 8 under 35 U.S.C. §103(a) as allegedly unpatentable over the Applicants' Admitted Prior Art Figures in view of Usami, et al. and further in view of U.S. Patent No. 5,429,995 to Nishiyama, et al. ("Nishiyama, et al."). Additionally, the Office Action has alleged that Claim 5 is a substantial duplicate of Claim 1 and advises